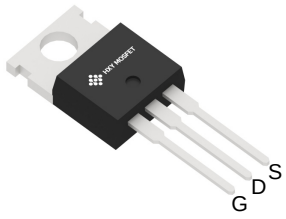
General Description

The DMTH10H005SCT use advanced SGT MOSFET technology toprovide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness.

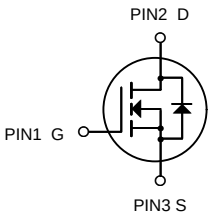


TO-220C

General Features

V_{DS} =100V I_D =120A

$R_{DS(ON)}$ < 5.0mΩ @ V_{GS}=10V



N-Channel MOSFET

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMTH10H005SCT	TO-220C	HXY MOSFET	50

Absolute Maximum Ratings at T_j=25℃ unless otherwise noted

Parameter		Symbol	Value	Unit
Drain source voltage		VDS	100	V
Gate source voltage		VGS	±20	V
Continuous drain current[1]	T_C=25°C	I_D	120	A
Continuous drain current[1]	T_C=100°C	I_D	81	A
Pulsed drain current[2]		I_{DM}	512	A
Power dissipation[4]		P_D	178	W
Single pulsed avalanche energy[3]		EAS	486	mJ
Operation and storage temperature		Tstg，Tj	-55 to 150	℃
Thermal resistance, junction-case		RθJC	0.8	°C/W
Thermal resistance, junction-ambient[4]		RθJA	56	°C/W

Electrical Characteristics（T_J = 25°C, unless otherwise noted）

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	4.1	5.0	mΩ
		V_{GS}=4.5V , I_D=20A	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=20A	---	35	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.6	---	Ω
Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=20A	---	69	---	nC
Q_{gs}	Gate-Source Charge		---	24	---	
Q_{gd}	Gate-Drain Charge		---	18.5	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=50V, RG=3Ω, ID=20A	---	18.0	---	ns
T_r	Rise Time		---	23	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37	---	
T_f	Fall Time		---	15.7	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	4102	---	pF
C_{oss}	Output Capacitance		---	592	---	
C_{rss}	Reverse Transfer Capacitance		---	19.8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	120	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is TJ = 25°C, L = 3.0mH, IAS = 18A, VGS = 10V, VDD = 50V; 100% test at L = 0.1mH, IAS = 67A.

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

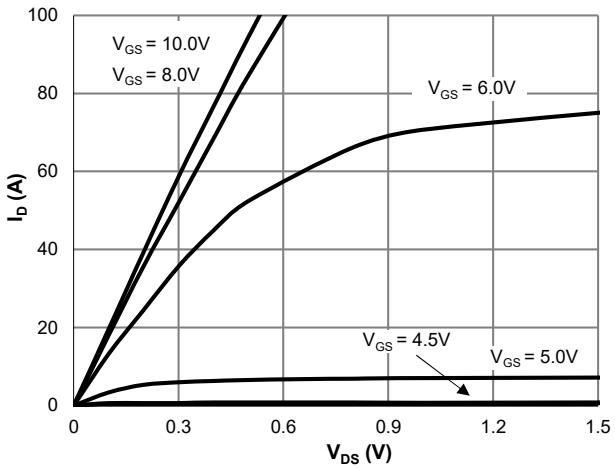


Figure 1: Saturation Characteristics

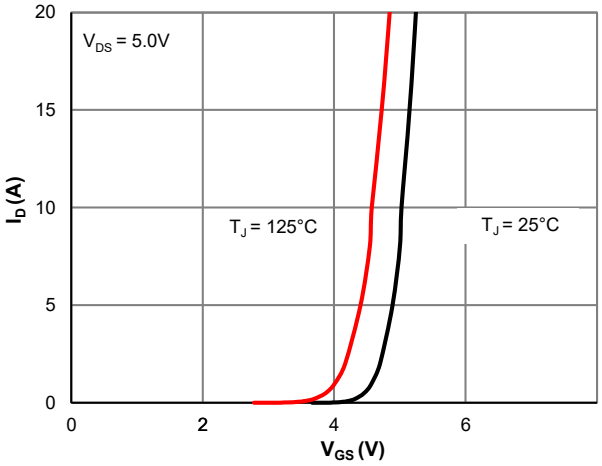


Figure 2: Transfer Characteristics

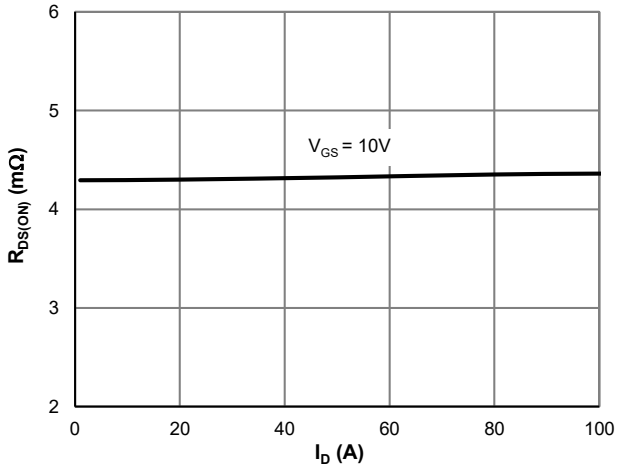


Figure 3: $R_{DS(ON)}$ vs. Drain Current

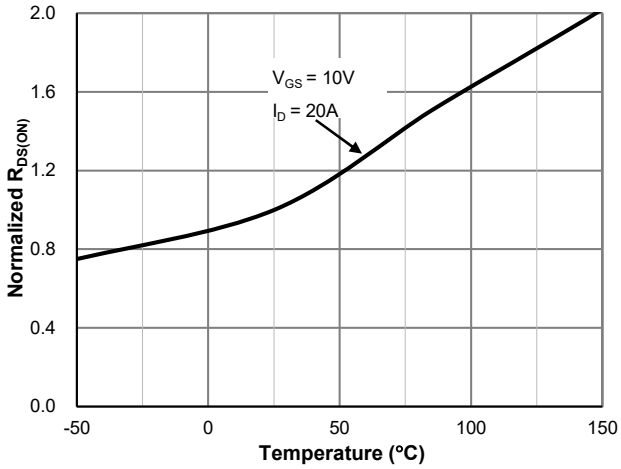


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

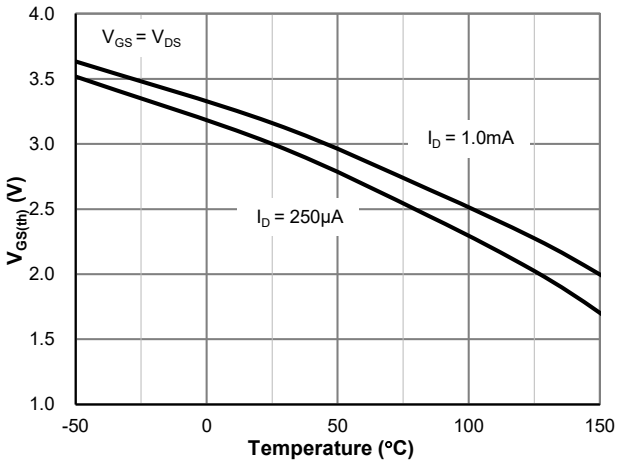


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

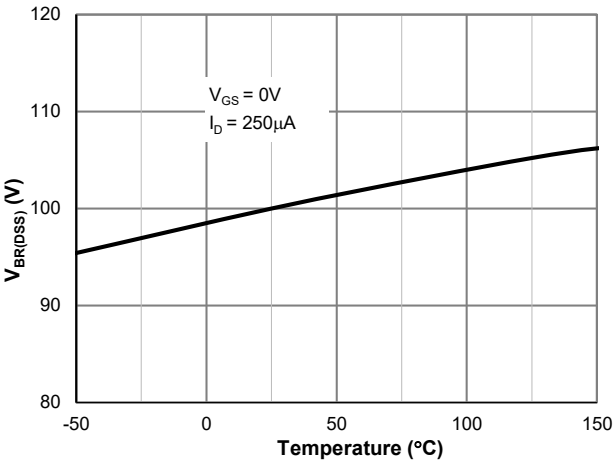


Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

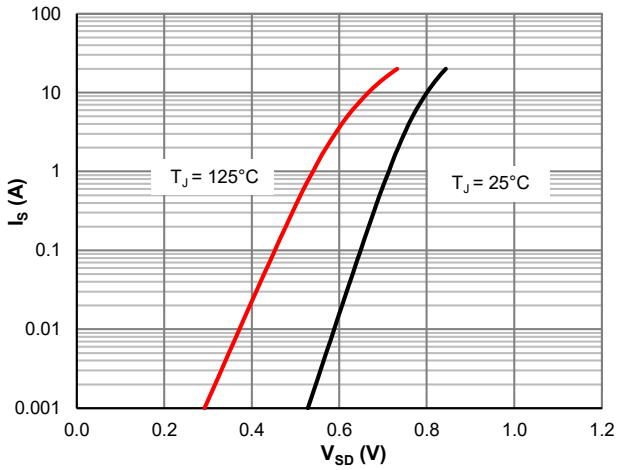


Figure 7: Body-Diode Characteristics

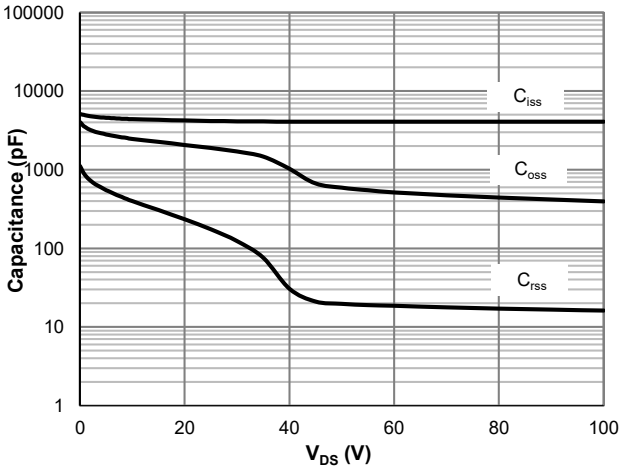


Figure 8: Capacitance Characteristics

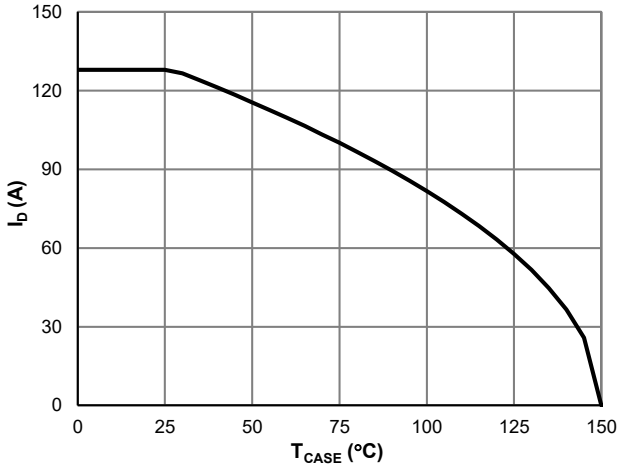


Figure 9: Current De-rating

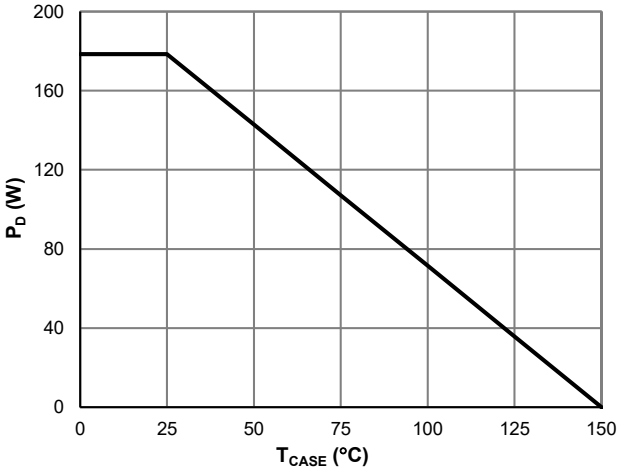


Figure 10: Power De-rating

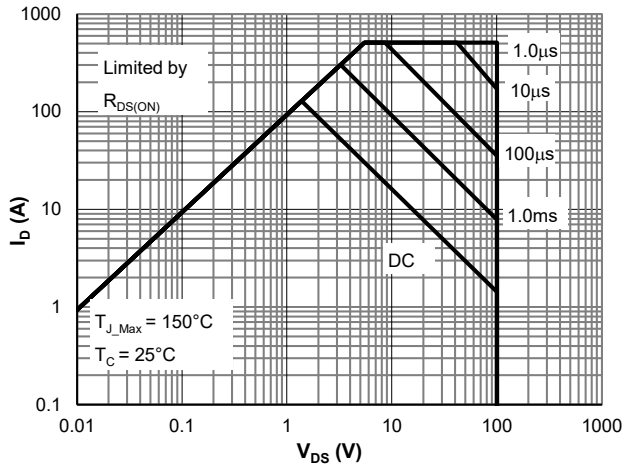


Figure 11: Maximum Safe Operating Area

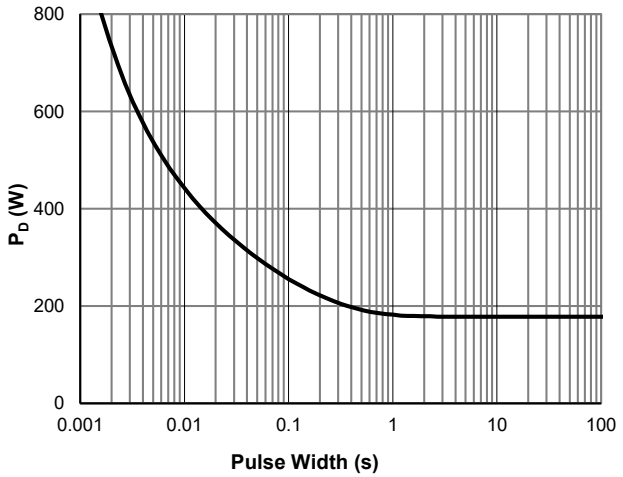


Figure 12: Single Pulse Power Rating, Junction-to-Case

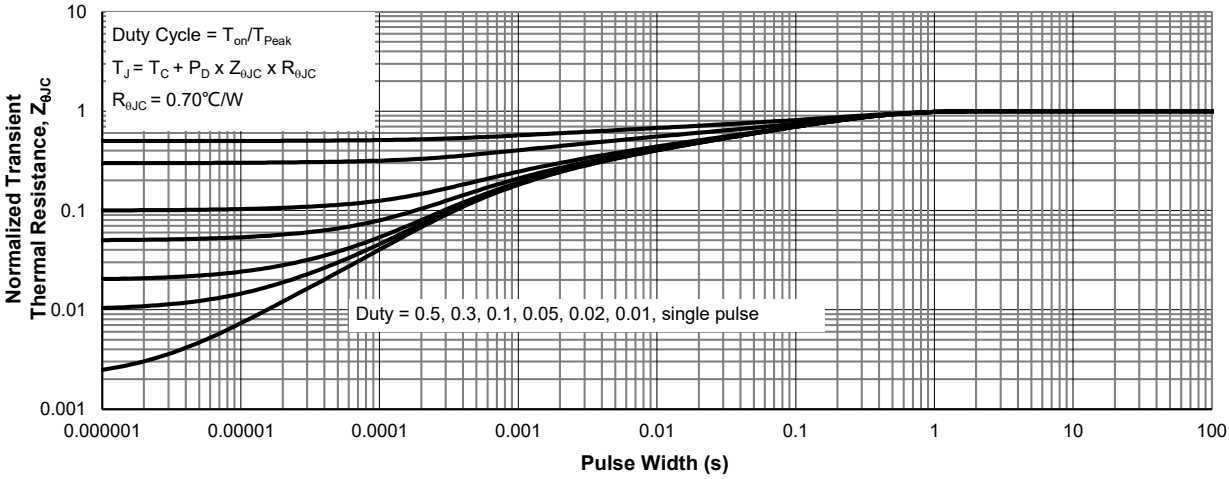
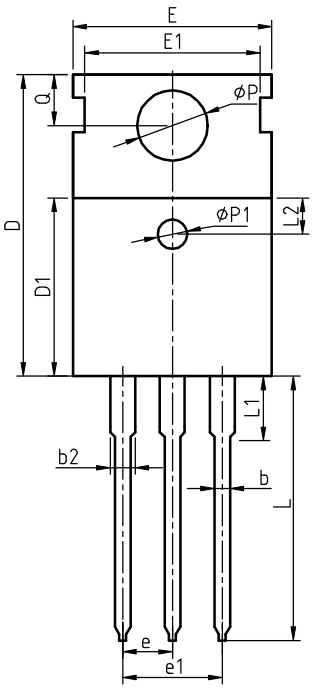
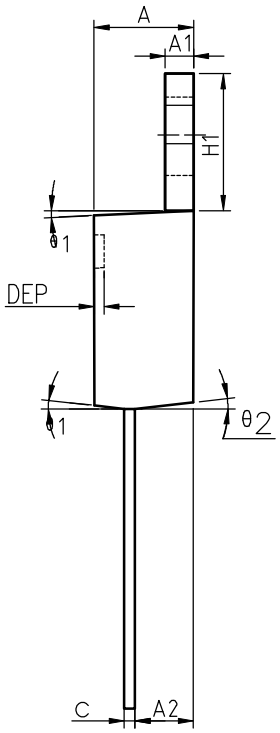


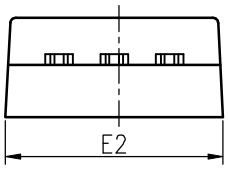
Figure 13: Normalized Maximum Transient Thermal Impedance

Package Information

TO-220C







COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
θ3	1°	3°	5°	1°	3°	5°

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